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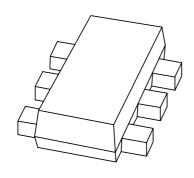
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PBSS4140V 40 V low V_{CEsat} NPN transistor

Product data sheet Supersedes data of 2001 Nov 05 2002 Jun 20



40 V low V_{CEsat} NPN transistor

PBSS4140V

FEATURES

- 300 mW total power dissipation
- Very small 1.6 mm x 1.2 mm x 0.55 mm ultra thin package
- · Improved thermal behaviour due to flat leads
- · Excellent coplanarity due to straight leads
- Low collector-emitter saturation voltage
- · High current capabilities
- Reduced required PCB area.

APPLICATIONS

- · General purpose switching and muting
- · LCD backlighting
- · Supply line switching circuits
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

DESCRIPTION

NPN low V_{CEsat} transistor with high current capability in a SOT666 plastic package. PNP complement: PBSS5140V.

MARKING

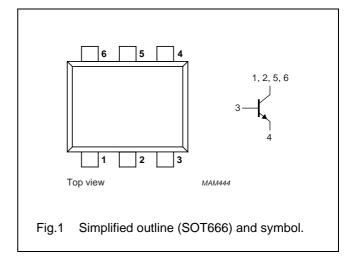
TYPE NUMBER	MARKING CODE
PBSS4140V	22

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	40	V
I _C	collector current (DC)	1	Α
I _{CRP}	RP peak collector current		Α
R _{CEsat} equivalent on-resistance		<190	mΩ

PINNING

PIN	DESCRIPTION	
1	collector	
2	collector	
3	base	
4	emitter	
5	collector	
6	collector	



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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	40	V
V_{CEO}	collector-emitter voltage	open base	-	40	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current (DC)		-	1	Α
I _{CM}	peak collector current		-	3	Α
I _{CRP}	repetitive peak collector current	note 1	_	2	Α
I _B	base current (DC)		_	300	mA
I _{BM}	peak base current		-	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 2	_	300	mW
		T _{amb} ≤ 25 °C; note 3	_	500	mW
		T _{amb} ≤ 25 °C; notes 1 and 2	_	1.2	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Operated under pulsed conditions: $t_p \le 30$ ms; $\delta \le 0.2$.
- 2. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.
- 3. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	410	K/W
		note 2	215	K/W
		notes 1 and 3	110	K/W

Notes

- 1. Device mounted on a printed circuit board; single sided copper; tinplated; standard footprint.
- 2. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².
- 3. Operated under pulsed conditions: $t_p \le 30$ ms; $\delta \le 0.2$.

Soldering

The only recommended soldering method is reflow soldering.

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CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

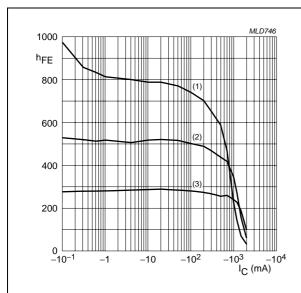
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 40 V; I _E = 0	_	_	100	nA
		V _{CB} = 40 V; I _E = 0; T _{amb} = 150 °C	_	_	50	μΑ
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0$	_	_	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0$	_	_	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	300	_	_	
		$V_{CE} = 5 \text{ V}; I_{C} = 500 \text{ mA}$	300	_	900	
		V _{CE} = 5 V; I _C = 1 A	200	_	_	
		V _{CE} = 5 V; I _C = 2 A; note 1	75	_	_	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 100 \text{ mA}; I_B = 1 \text{ mA}$	_	50	80	mV
		$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	_	70	110	mV
		I _C = 1 A; I _B = 100 mA; note 1	_	150	190	mV
		$I_C = 2 \text{ A}$; $I_B = 200 \text{ mA}$; note 1	_	320	440	mV
R _{CEsat}	equivalent on-resistance	$I_C = 1 \text{ A}$; $I_B = 100 \text{ mA}$; note 1	_	150	<190	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = 1 A; I _B = 100 mA	_	-	1.2	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = 5 V; I _C = 1 A	_	_	1.1	٧
f _T	transition frequency	$I_C = 50 \text{ mA}; V_{CE} = 10 \text{ V};$ f = 100 MHz	150	_	_	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	_	10	pF

Note

1. Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

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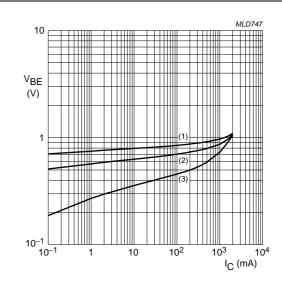
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V_{CE} = 5 V.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

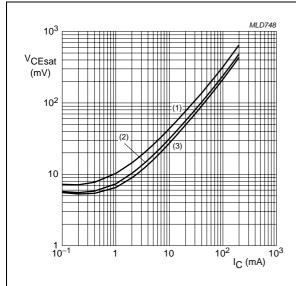
Fig.2 DC current gain as a function of collector current; typical values.



 $V_{CE} = 5 V.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

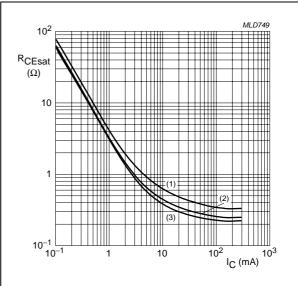
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.5 Equivalent on-resistance as a function of collector current; typical values.

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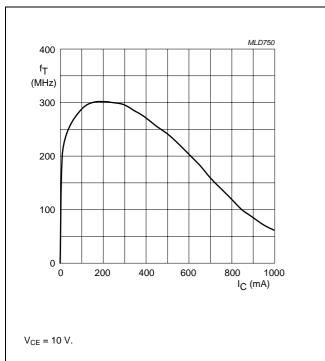


Fig.6 Transition frequency as a function of collector current.

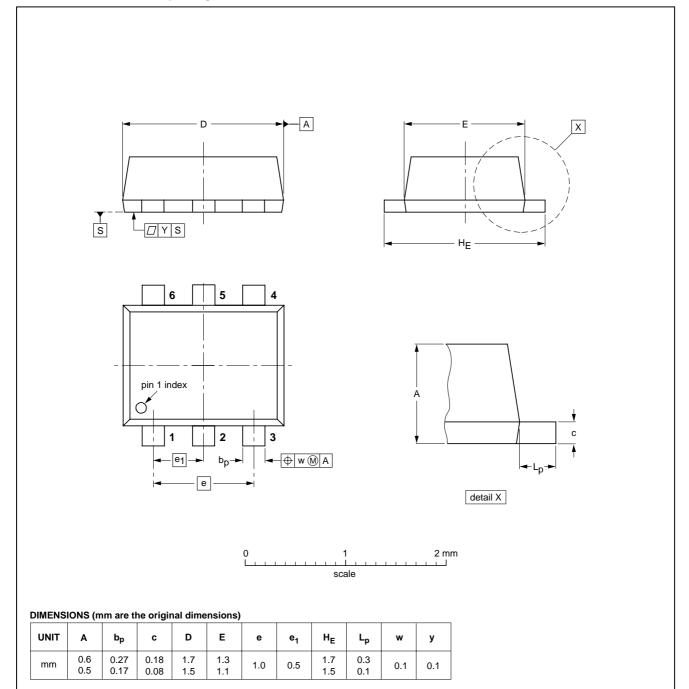
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



OUTLINE	REFERENCES			REFERENCES EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						-01-01-04 01-08-27
	I .					

40 V low V_{CEsat} NPN transistor

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

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Contact information

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